1. Scope :

This specification applies to N/P silicon zener diode chips,
Device NO. SD-40814G

2. Structure :

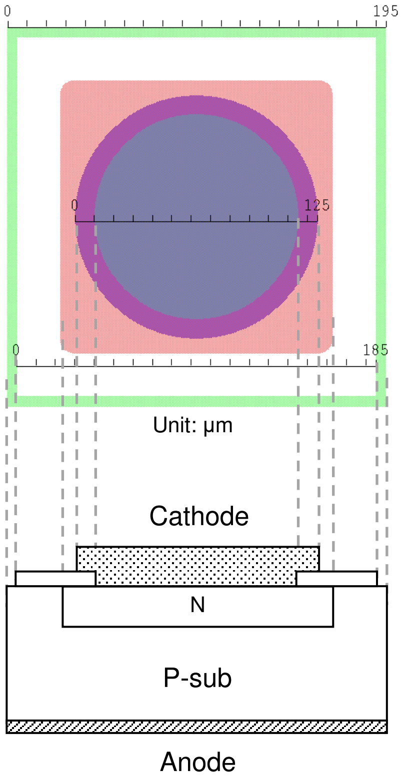
2-1. Planar type : N/P Diode
2-2. Electrodes :
Top side : Gold Pad.
Back side : Gold Layer.

3. Size :

3-1. Chip size : 195 ± 20 µm x 195 ± 20 µm (7.8 ± 0.8 mils x 7.8 ± 0.8 mils).
3-2. Chip thickness : 100 ± 20 µm (4.0 ± 0.8 mils).
3-3. Bonding pad : ϕ 125 ± 10 µm (ϕ 5.0 ± 0.4 mils).
3-4. Pattern drawing : Refer to the attached drawing.

4. Electrical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I_R	V_R=5V Ee=0mW/cm^2			500	nA
Zener Voltage	V_Z	I_Z=5mA Ee=0mW/cm^2	12		16	V
Forward Voltage	V_F	I_F=10mA Ee=0mW/cm^2	800		1200	mV



Equivalent Circuit